WANSEMI
万芯半导体

WX05P04

Enhancement Mode P-Channel Power MOSFET

SOT23/PMOS/-40V/±20V/-1.6V/-5A/62mΩ

Rev1.0

-40V, 62mΩ, -5A, Single P-Channel

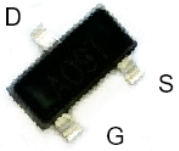
1.Features

- -40V MOSFET technology
- Low on-state resistance
- Fast switching
- Vgs±20V

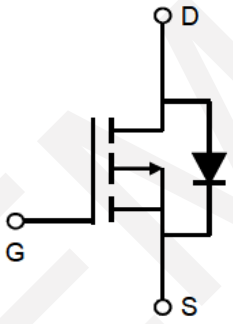
V_{DS}	$R_{DS(on)}$ Typ.	I_D Max.
-40V	62mΩ @ -10V	-5A
	79mΩ @ -4.5V	

2.Applications

- Power Switching Application
- Load Switching



SOT23
Pin Description



Schematic Diagram

3.Package Marking and Ordering Information

Part no.	Marking	Package	PCS/Reel	PCS/CTN.
WX05P04	05P04	SOT23	3,000	120,000

4.Absolute Max Ratings at Ta=25℃ (Note1)

Parameter	Symbol	Maximum	Units
Drain to Source Voltage	V_{DSS}	-40	V
Gate to Source Voltage	V_{GSS}	±20	V
Drain Current (DC)	I_D	-5	A
Drain Current (Pulse), PW≤300μs	I_{DP}	-20	A
Total Dissipation	P_D	1.2	W
Junction Temperature	T_j	150	℃
Storage Temperature	T_{stg}	-55 to +150	℃

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

5.Thermal Resistance Ratings (Note 2)

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	103	℃/W

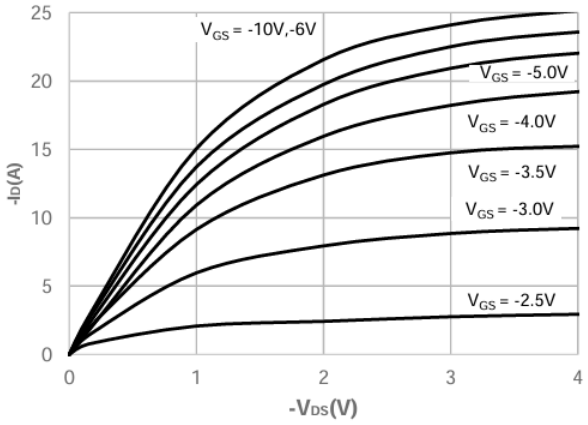
Note 2: When mounted on 1 inch square copper board t ≤ 10sec The value in any given application depends on the user's specific board design.

6.Electrical Characteristics at Ta=25℃ (Note 3)

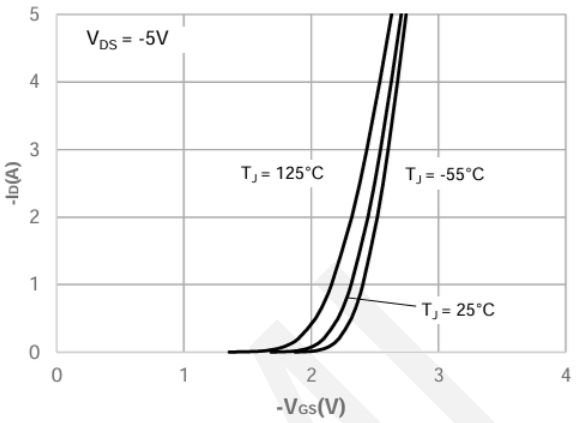
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	I_D = -250μA, V_{GS} = 0V	-40	-	-	V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS} = -40V, V_{GS} = 0V	-	-	-1	μA
Gate to Source Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V	-	-	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_{DS}=-250μA	-1	-1.6	-2.5	V
Static Drain to Source On-State Resistance	$R_{DS(on)}$	I_D = -3A, V_{GS} = 10V	-	62	80	mΩ
		I_D = -2A, V_{GS} = 4.5V	-	79	105	mΩ
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=-20V, Frequency=1.0MHz	-	546	-	pF
Output Capacitance	C_{oss}		-	52	-	pF
Reverse Transfer Capacitance	C_{rss}		-	43	-	pF
Turn-ON Delay Time	$t_{d(on)}$	V_{DD} = -20V, I_D=-2A, V_{GS} = -10V, R_{GEN} = 3Ω	-	8	-	ns
Rise Time	t_r		-	13	-	ns
Turn-OFF Delay Time	$t_{d(off)}$		-	16	-	ns
Fall Time	t_f		-	6	-	ns
Total Gate Charge	Q_g	V_{DS} = -20V, V_{GS} =0 to 10V, I_D = -2A	-	11	-	nC
	Q_{gs}		-	1.8	-	nC
	Q_{gd}		-	1.9	-	nC
Diode Forward Voltage	V_{FSD}	I_S = -3A, V_{GS} = 0	0.5	-	1.2	V

Note 3: Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

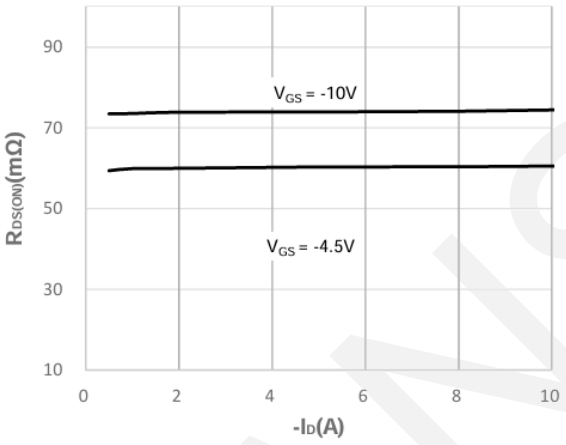
7.Typical Electrical and Thermal Characteristics



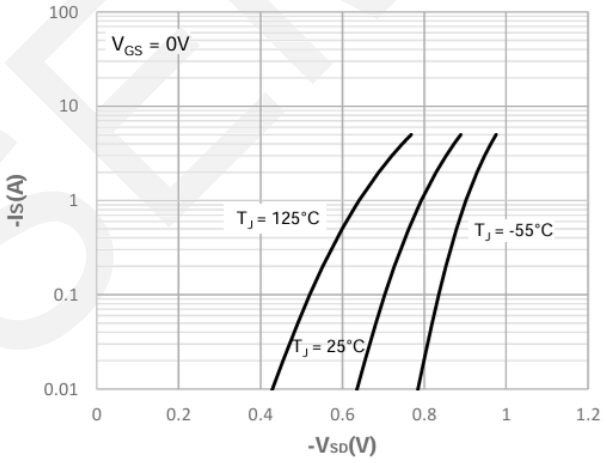
Output Characteristics



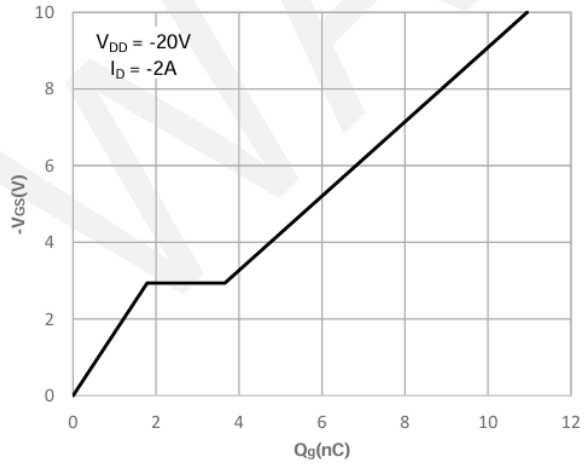
Transfer Characteristics



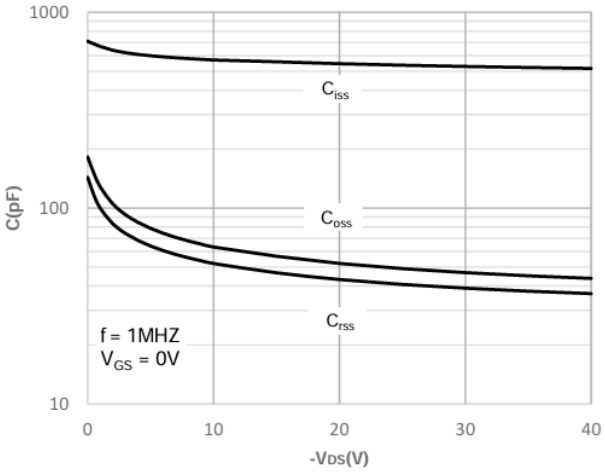
Drain-Source On-Resistance



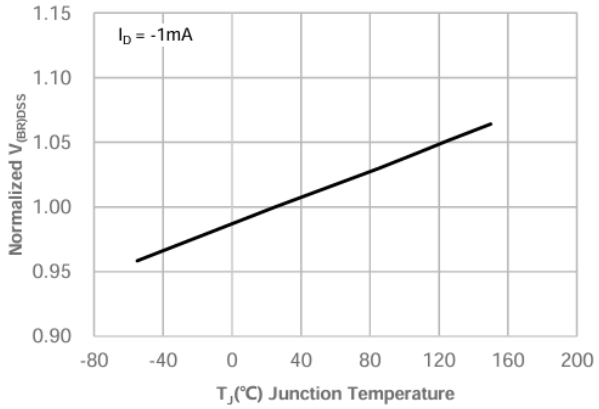
Body Diode Characteristics



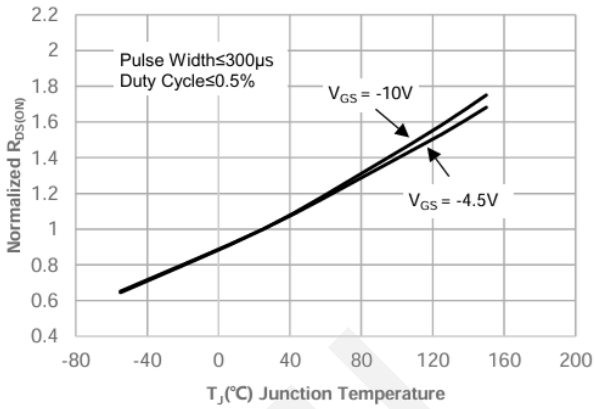
Gate Charge Characteristics



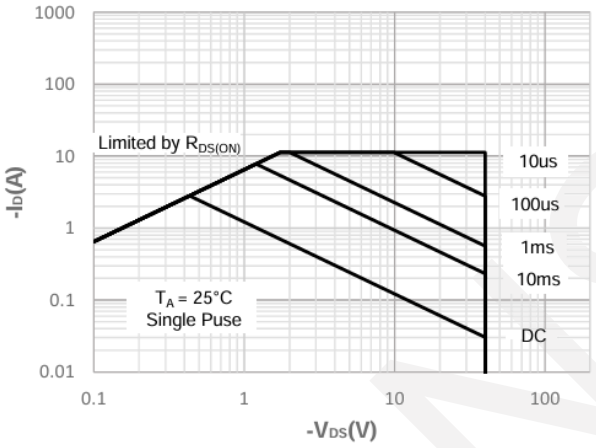
Capacitance Characteristics



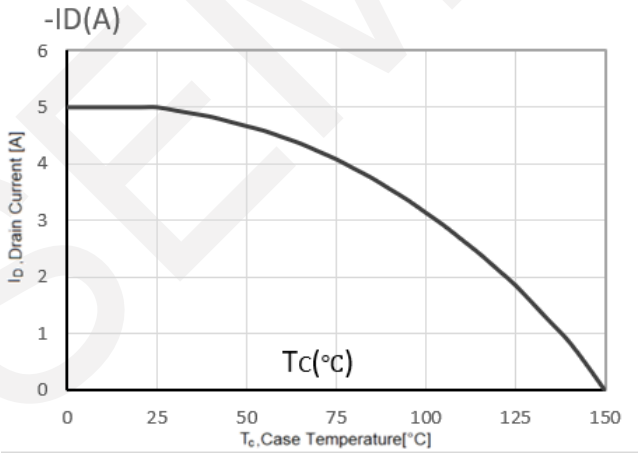
Normalized Breakdown voltage vs. Junction Temperature



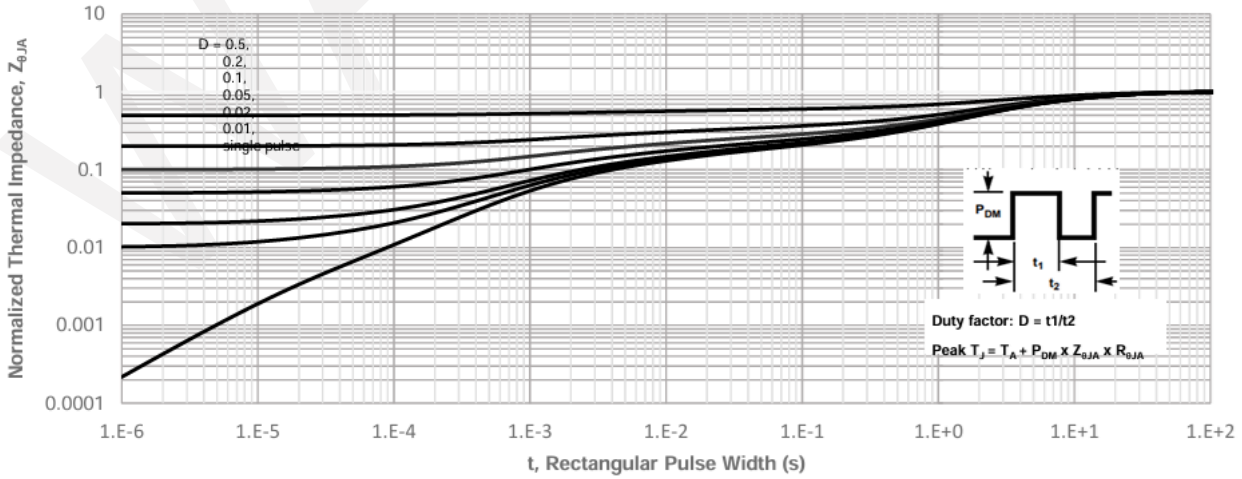
Normalized on Resistance vs. Junction Temperature



Maximum Safe Operating Area

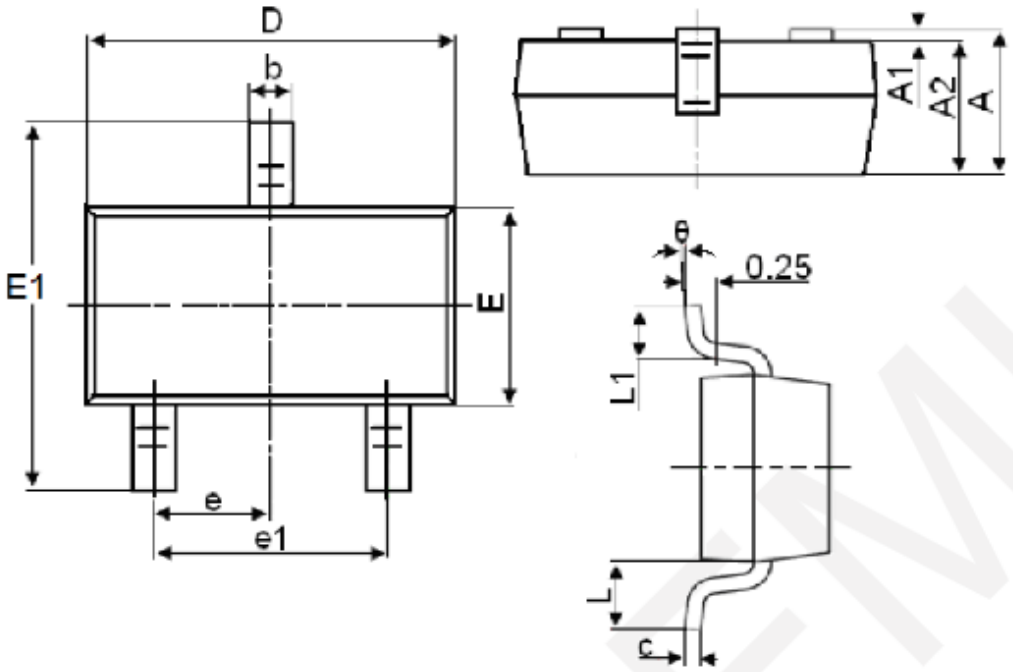


Maximum Continuous Drian Current vs. Ambient Temperature



Normalized Maximum Transient Thermal Impedance

8.Package Dimensions



Symbol	Dimensions in Millimeters		
	MIN.	TYP.	MAX.
A	0.900		1.150
A1	0.000		0.100
A2	0.900		1.050
b	0.300		0.500
c	0.080		0.150
D	2.800		3.000
E	1.200		1.400
E1	2.250		2.550
e		0.950	
e1	1.800		2.000
L		0.550	
L1	0.300		0.500
θ	0°		8°

9. Important Notice

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